

# MOSFET – Power, Single N-Channel

## 100 V, 5.1 mΩ, 108 A

### NVMYS005N10MCL

#### Features

- Small Footprint (5x6 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free, Beryllium Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	100	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$ 108 A
		$T_C = 100^\circ\text{C}$	76
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	$P_D$ 131 W
		$T_C = 100^\circ\text{C}$	65
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$ 18.4 A
		$T_A = 100^\circ\text{C}$	13.0
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$ 3.8 W
		$T_A = 100^\circ\text{C}$	1.9
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	$I_{DM}$ 736	A
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	100	A
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 6.5 \text{ A}$ )	$E_{AS}$	365	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$

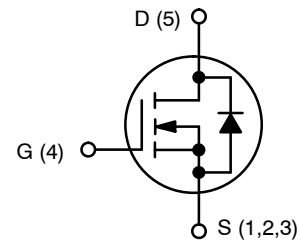
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	1.15	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	40	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using 1 in<sup>2</sup> pad size, 2 oz. Cu pad.

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
100 V	5.1 mΩ @ 10 V	108 A
	7.1 mΩ @ 4.5 V	

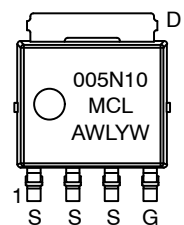


N-CHANNEL MOSFET



LFPAK4  
CASE 760AB

#### MARKING DIAGRAM



- 005N10MCL = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- W = Work Week

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

# NVMYS005N10MCL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA, ref to 25°C		52		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V	T <sub>J</sub> = 25°C		1	μA
			T <sub>J</sub> = 125°C		100	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V			100	nA

## ON CHARACTERISTICS

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 192 μA	1		3	V
Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>	I <sub>D</sub> = 192 μA, ref to 25°C		-5.6		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 34 A		4.2	5.1	mΩ
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 27 A		5.6	7.1	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 50 A		155		S
Gate-Resistance	R <sub>G</sub>	T <sub>A</sub> = 25°C		0.85		Ω

## CHARGES & CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 50 V		4100		pF	
Output Capacitance	C <sub>OSS</sub>			1350			
Reverse Transfer Capacitance	C <sub>RSS</sub>			22			
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 50 V, I <sub>D</sub> = 34 A		26		nC	
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 50 V, I <sub>D</sub> = 34 A		55		nC	
Gate-to-Source Charge	Q <sub>GS</sub>			11			
Gate-to-Drain Charge	Q <sub>GD</sub>			5			
Plateau Voltage	V <sub>GP</sub>			3			V
Threshold Gate Charge	Q <sub>G(TH)</sub>			6			nC

## SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 50 V, I <sub>D</sub> = 34 A, R <sub>G</sub> = 6 Ω		17		ns
Rise Time	t <sub>r</sub>			6.7		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			57		
Fall Time	t <sub>f</sub>			12.3		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 34 A	T <sub>J</sub> = 25°C		0.85	1.3	V
			T <sub>J</sub> = 125°C		0.73		
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, di/dt = 100 A/μs, I <sub>S</sub> = 17 A		56		ns	
Reverse Recovery Charge	Q <sub>RR</sub>			54		nC	
Charge Time	t <sub>a</sub>			25		ns	
Discharge Time	t <sub>b</sub>			31		ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

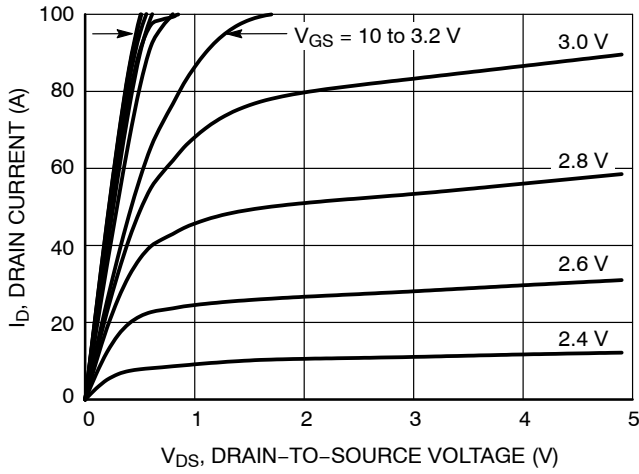


Figure 1. On-Region Characteristics

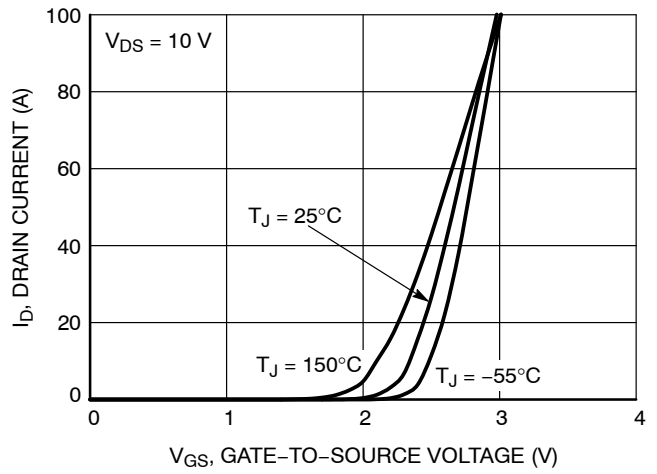


Figure 2. Transfer Characteristics

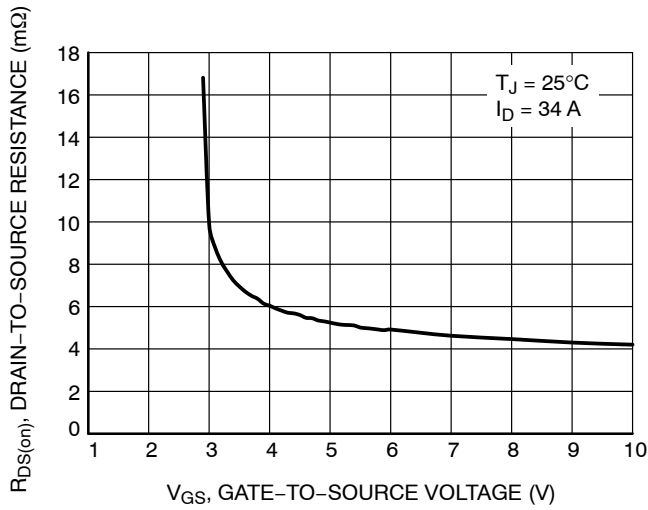


Figure 3. On-Resistance vs. Gate-to-Source Voltage

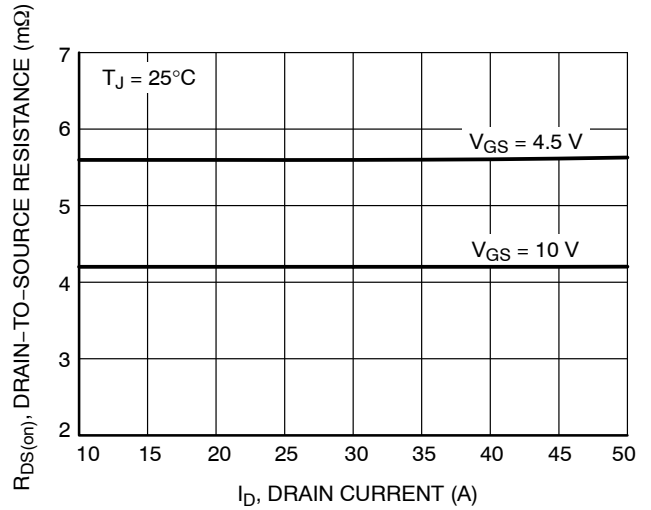


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

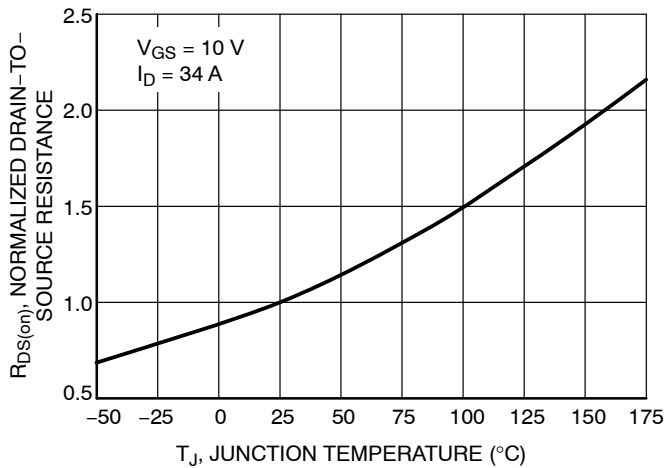


Figure 5. On-Resistance Variation with Temperature

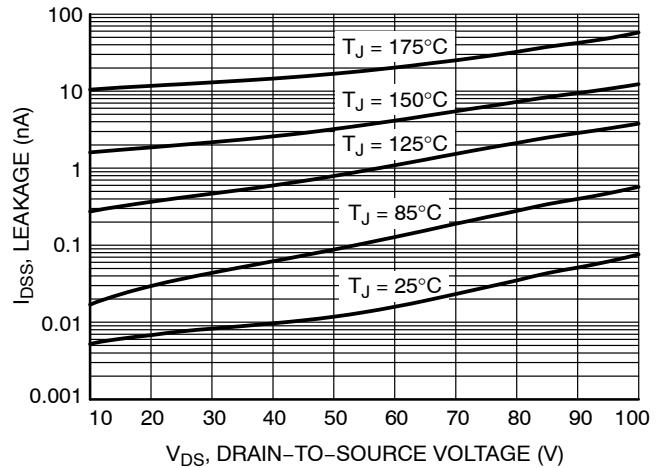


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NVMYS005N10MCL

## TYPICAL CHARACTERISTICS

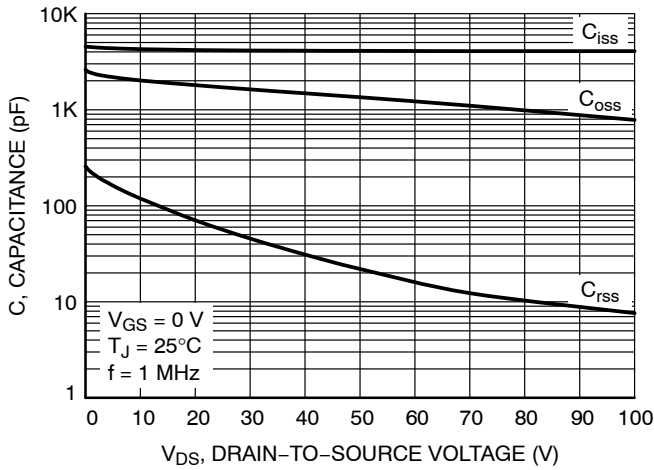


Figure 7. Capacitance Variation

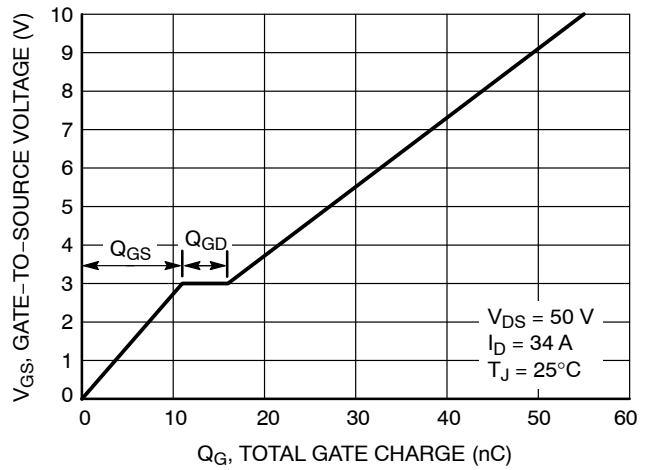


Figure 8. Gate-to-Source vs. Total Charge

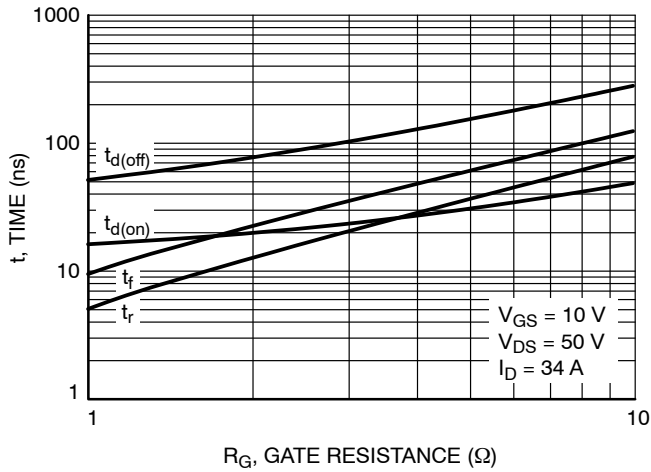


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

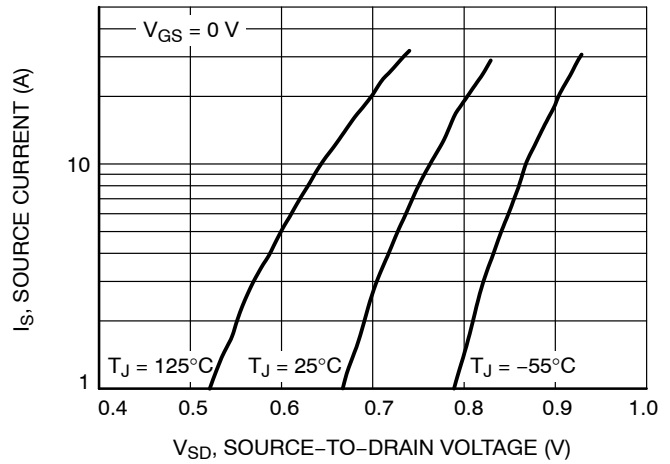


Figure 10. Diode Forward Voltage vs. Current

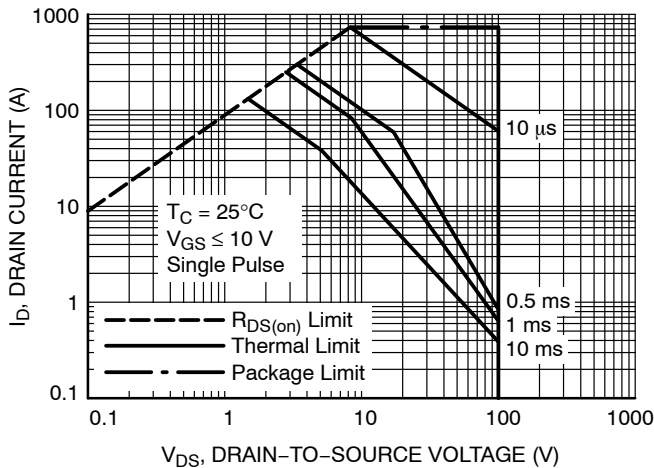


Figure 11. Maximum Rated Forward Biased Safe Operating Area

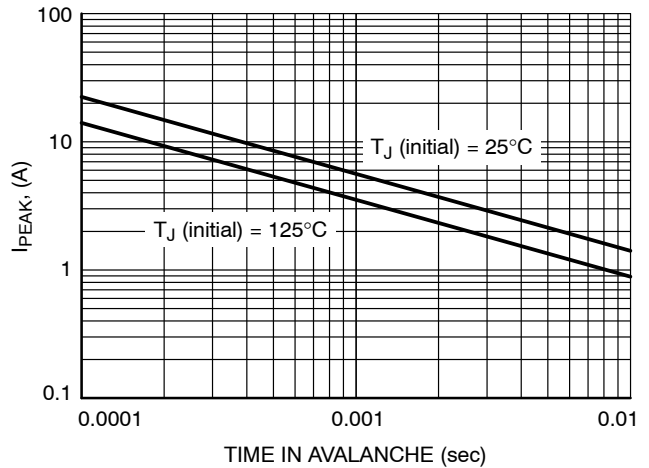


Figure 12. Maximum Drain Current vs. Time in Avalanche

# NVMYS005N10MCL

## TYPICAL CHARACTERISTICS

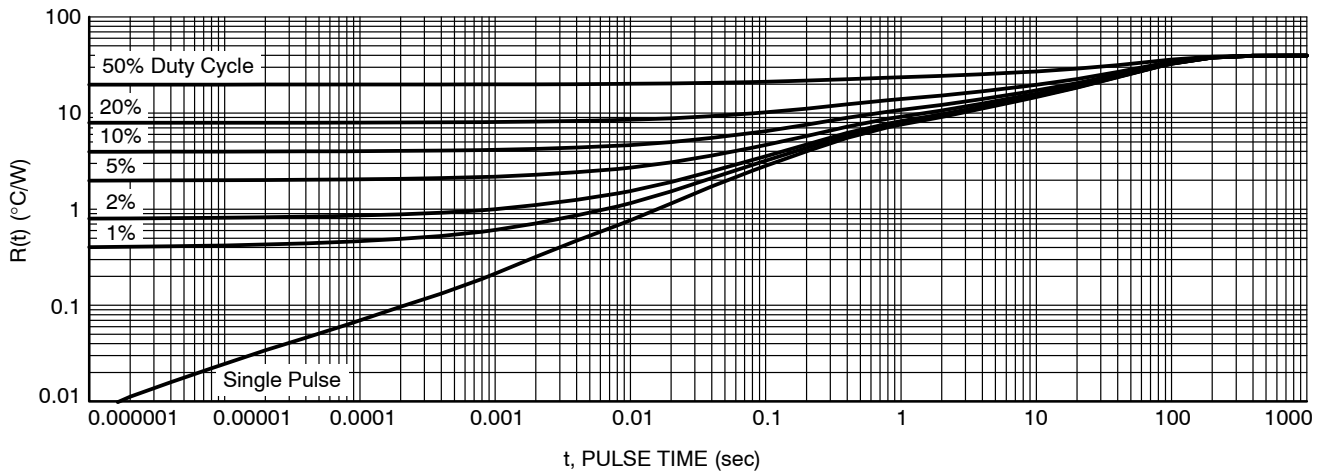


Figure 13. Thermal Response

### DEVICE ORDERING INFORMATION

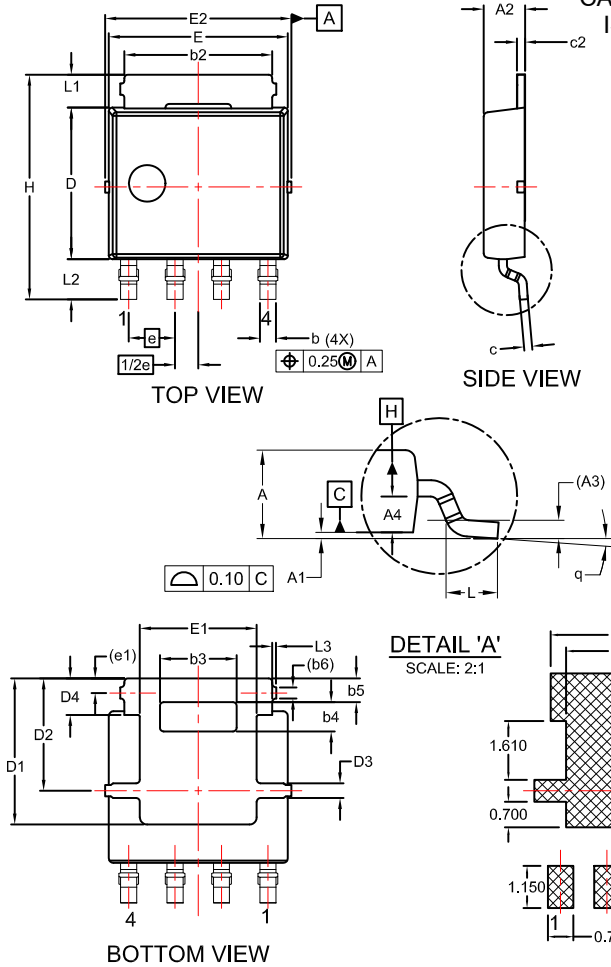
Device	Marking	Package	Shipping <sup>†</sup>
NVMYS005N10MCLTWG	005N10MCL	LFPAK4 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NVMYS005N10MCL

## PACKAGE DIMENSIONS

LFP4K4 5x6  
CASE 760AB  
ISSUE C



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

UNIT IN MILLIMETER			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3	0.25 REF		
A4	0.45	0.50	0.55
b	0.40	0.45	0.50
b2	3.80	4.10	4.40
b3	2.00	2.10	2.20
b4	0.70	0.80	0.90
b5	0.55	0.65	0.75
b6	0.31 REF		
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.05	4.15	4.25
D1	3.80	4.00	4.20
D2	3.00	3.10	3.20
D3	0.30	0.40	0.50
D4	0.90	1.00	1.10
E	4.80	4.90	5.00
E1	3.10	3.20	3.30
E2	5.00	5.15	5.30
e	1.27 BSC		
1/2e	0.635 BSC		
e1	0.40 REF		
H	6.00	6.15	6.30
L	0.40	0.65	0.85
L1	0.80	0.90	1.00
L2	0.90	1.10	1.30
L3	0.00	0.10	0.20
q	0°	4°	8°

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:  
Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

onsemi Website: [www.onsemi.com](http://www.onsemi.com)

TECHNICAL SUPPORT  
North American Technical Support:  
Voice Mail: 1 800-282-9855 Toll Free USA/Canada  
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:  
Phone: 00421 33 790 2910  
For additional information, please contact your local Sales Representative